

What is claimed is:

1. A method of manufacturing a semiconductor device including a laser chip and a base having the laser chip mounted thereon, including the step of:

irradiating the base with an energy beam having a shorter wavelength than an oscillation wavelength of the laser chip.

2. A method of manufacturing a semiconductor device according to claim 1 including the step of:

shutting off the base from the outside, after the step of irradiating the base with the energy beam.

3. A method of manufacturing a semiconductor device according to claim 1, wherein a laser chip having a nitride semiconductor layer is used as the laser chip.

4. A method of manufacturing a semiconductor device according to claim 1, wherein a laser chip having an oscillation wavelength of 550 nm or less is used as the laser chip.

5. A method of manufacturing a semiconductor device according to claim 1, wherein irradiation takes place using laser light or ultraviolet light as the energy beam.

6. A method of manufacturing a semiconductor device including a laser chip and a base, including the step of:

irradiating the base having the laser chip mounted thereon with plasma.

7. A method of manufacturing a semiconductor device according to claim 6 including the step of:

shutting off the base from the outside, after the step of irradiating the base with the plasma.

8. A method of manufacturing a semiconductor device according to claim 6, wherein a laser chip having a nitride semiconductor layer is used as the laser chip.

9. A method of manufacturing a semiconductor device according to claim 6, wherein a laser chip having an oscillation wavelength of 550 nm or less is used as the laser chip.

10. A method of manufacturing a semiconductor device according to claim 6, wherein the step of irradiating the base with the plasma takes place in an atmosphere of oxygen.